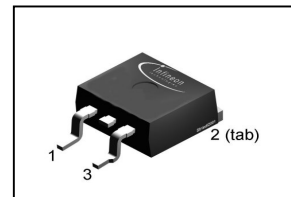


OptiMOS™ -T2 Power-Transistor
Features

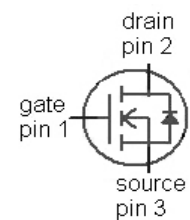
- N-channel - Enhancement mode
- Automotive AEC Q101 qualified
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- **Green package (lead free)**
- 100% Avalanche tested

Product Summary

V_{DS}	40	V
$R_{DS(on),max}$	3.6	mΩ
I_D	120	A

PG-TO263-3-2


Type	Package	Ordering Code	Marking
IPB120N04S4-04	PG-TO263-3-2	-	4N0404


Maximum ratings, at $T_j=25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$T_C=25^\circ\text{C}, V_{GS}=10\text{V}$	120	A
		$T_C=100^\circ\text{C}, V_{GS}=10\text{V}^{1)}$	91	
Pulsed drain current ¹⁾	$I_{D,pulse}$	$T_C=25^\circ\text{C}$	480	
Avalanche energy, single pulse	E_{AS}	$I_D=60\text{A}$	75	mJ
Avalanche current, single pulse	I_{AS}	-	120	A
Gate source voltage	V_{GS}	-	± 20	V
Power dissipation	P_{tot}	$T_C=25^\circ\text{C}$	79	W
Operating and storage temperature	T_j, T_{stg}	-	-55 ... +175	°C
IEC climatic category; DIN IEC 68-1		-	55/175/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics¹⁾						
Thermal resistance, junction - case	R_{thJC}		-	-	1.9	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}		-	-	62	
SMD version, device on PCB	R_{thJA}	minimal footprint	-	-	62	
		6 cm ² cooling area ²⁾	-	-	40	

Electrical characteristics, at $T_j=25^\circ\text{C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=1mA$	40	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=40\mu A$	2.0	3.0	4.0	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=40V, V_{GS}=0V, T_j=25^\circ\text{C}$	-	0.01	1	μA
		$V_{DS}=18V, V_{GS}=0V, T_j=85^\circ\text{C}^{2)}$	-	3	36	
Gate-source leakage current	I_{GSS}	$V_{GS}=20V, V_{DS}=0V$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=100A$	-	3.2	3.6	m Ω

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics¹⁾

Input capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=25V,$ $f=1MHz$	-	3150	4100	pF
Output capacitance	C_{oss}		-	770	1000	
Reverse transfer capacitance	C_{rss}		-	30	70	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=20V, V_{GS}=10V,$ $I_D=120A, R_G=3.5\Omega$	-	11	-	ns
Rise time	t_r		-	18	-	
Turn-off delay time	$t_{d(off)}$		-	9	-	
Fall time	t_f		-	15	-	

Gate Charge Characteristics¹⁾

Gate to source charge	Q_{gs}	$V_{DD}=32V, I_D=120A,$ $V_{GS}=0 \text{ to } 10V$	-	20	26	nC
Gate to drain charge	Q_{gd}		-	7	16	
Gate charge total	Q_g		-	42	55	
Gate plateau voltage	$V_{plateau}$		-	6.0	-	V

Reverse Diode

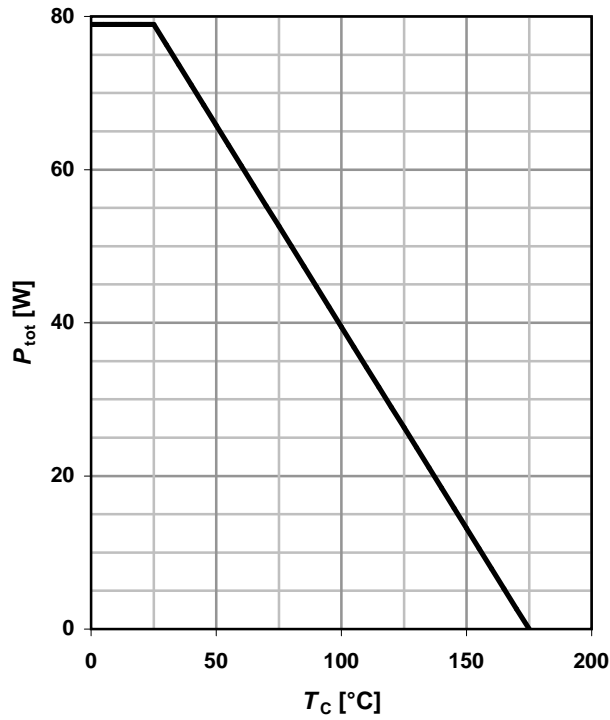
Diode continuous forward current ¹⁾	I_S	$T_C=25^\circ C$	-	-	120	A
Diode pulse current ¹⁾	$I_{S,pulse}$		-	-	480	
Diode forward voltage	V_{SD}	$V_{GS}=0V, I_F=100A,$ $T_J=25^\circ C$	-	0.9	1.3	V
Reverse recovery time ¹⁾	t_{rr}	$V_R=20V, I_F=I_S,$ $di_F/dt=100A/\mu s$	-	45	-	ns
Reverse recovery charge ¹⁾	Q_{rr}		-	50	-	nC

¹⁾ Defined by design. Not subject to production test.

²⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

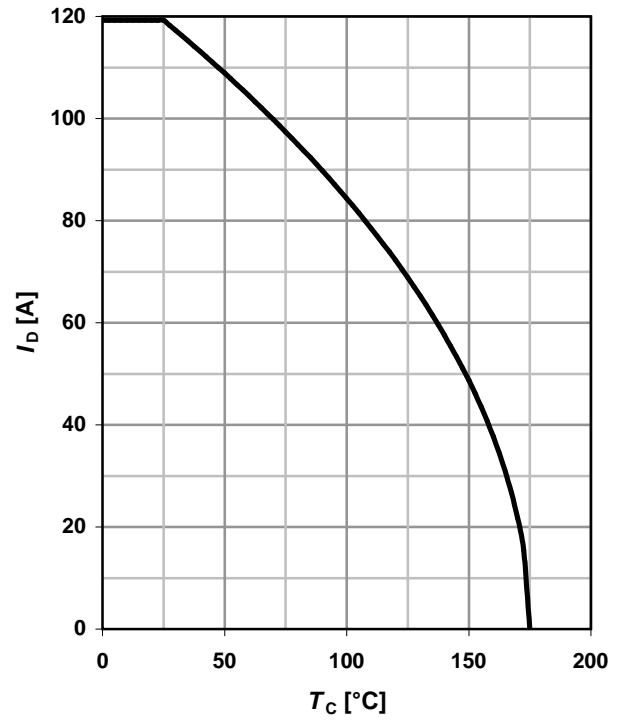
1 Power dissipation

$$P_{\text{tot}} = f(T_C); V_{\text{GS}} \geq 6 \text{ V}$$



2 Drain current

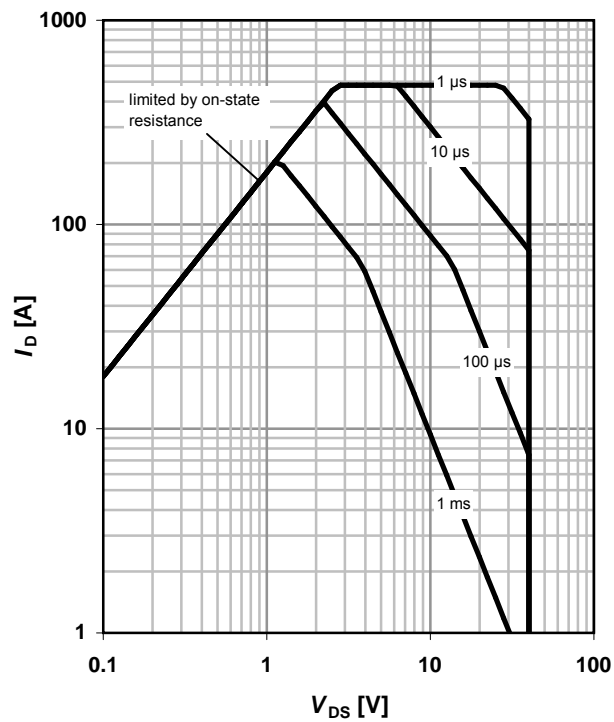
$$I_D = f(T_C); V_{\text{GS}} \geq 6 \text{ V}$$



3 Safe operating area

$$I_D = f(V_{\text{DS}}); T_C = 25 \text{ °C}; D = 0$$

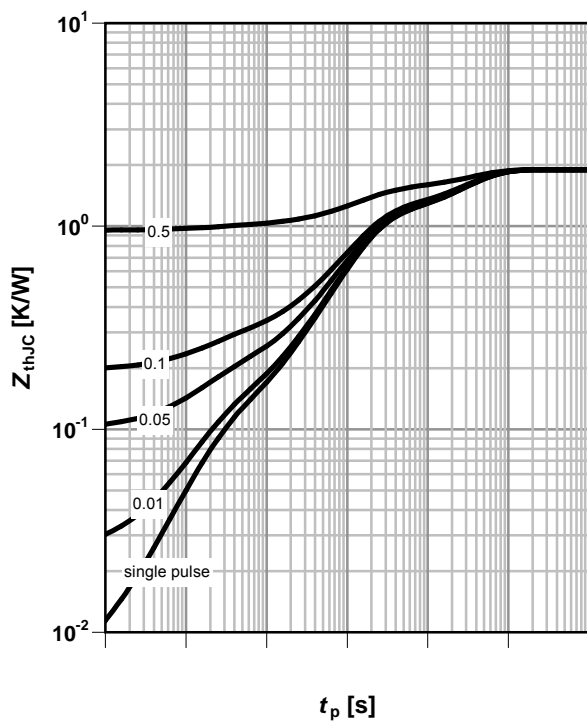
parameter: t_p



4 Max. transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

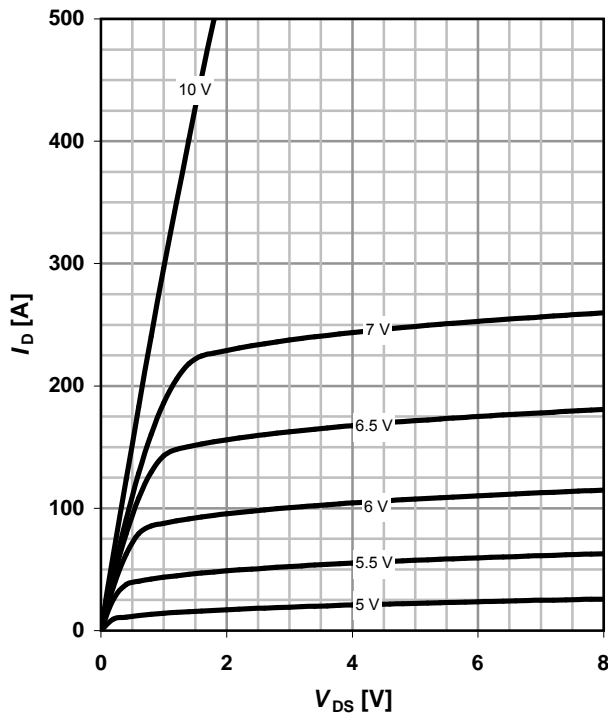
parameter: $D = t_p/T$



5 Typ. output characteristics

$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}$

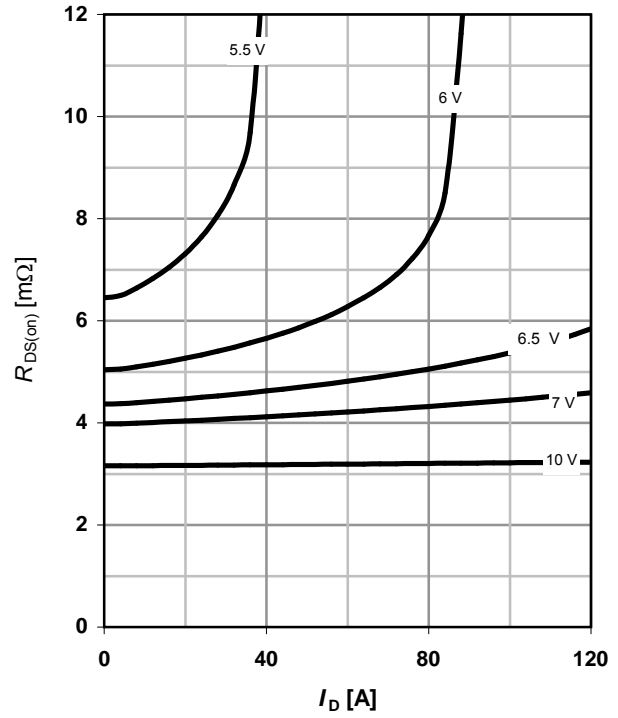
parameter: V_{GS}



6 Typ. drain-source on-state resistance

$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}$

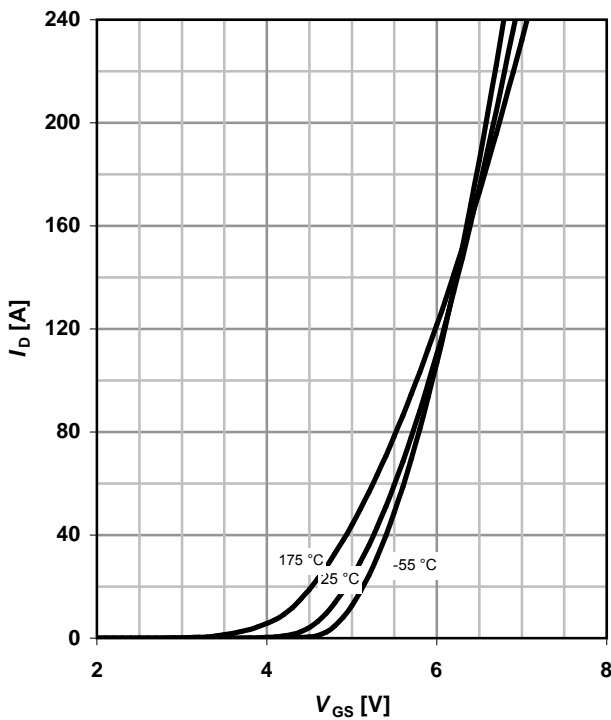
parameter: V_{GS}



7 Typ. transfer characteristics

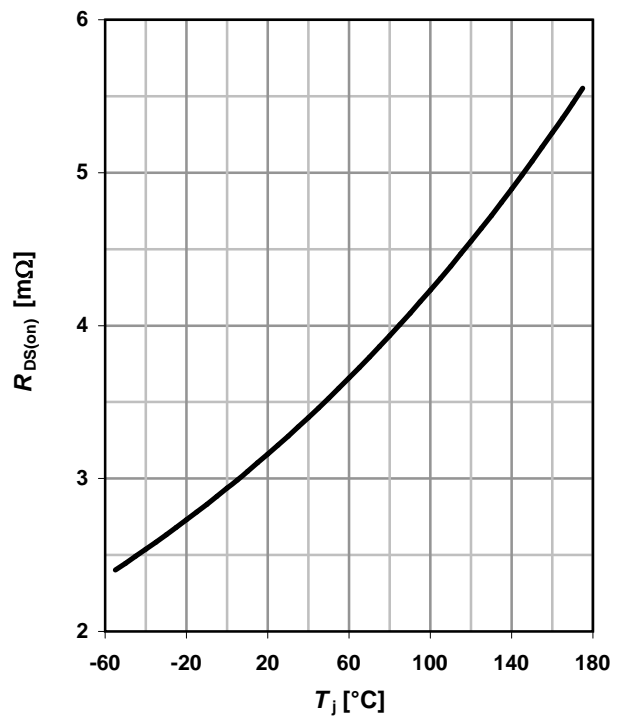
$I_D = f(V_{GS}); V_{DS} = 6\text{ V}$

parameter: T_j



8 Typ. drain-source on-state resistance

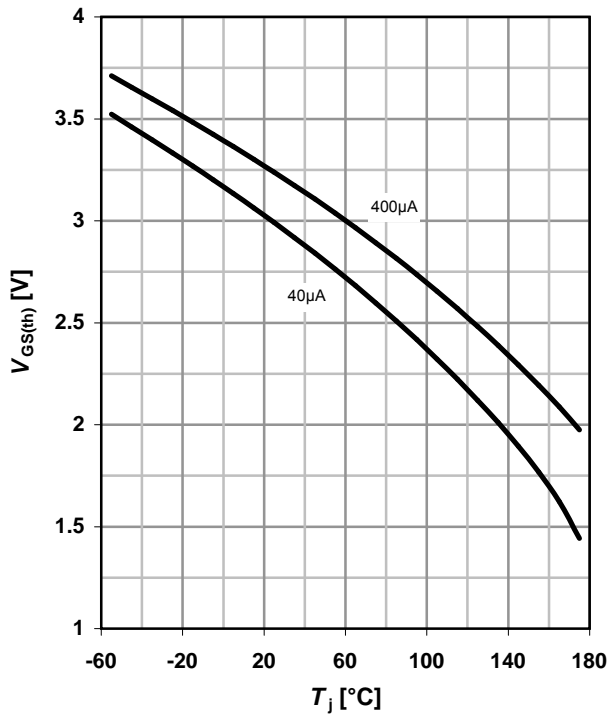
$R_{DS(on)} = f(T_j); I_D = 100\text{ A}; V_{GS} = 10\text{ V}$



9 Typ. gate threshold voltage

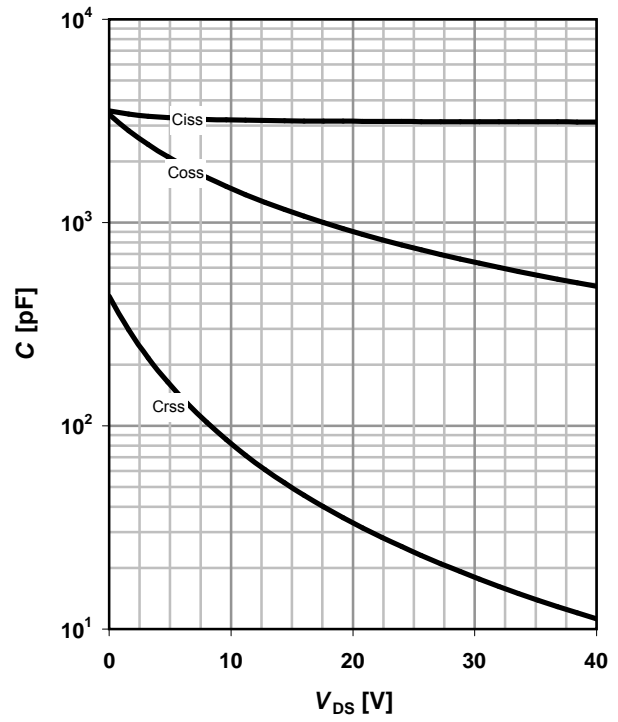
$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$

parameter: I_D



10 Typ. capacitances

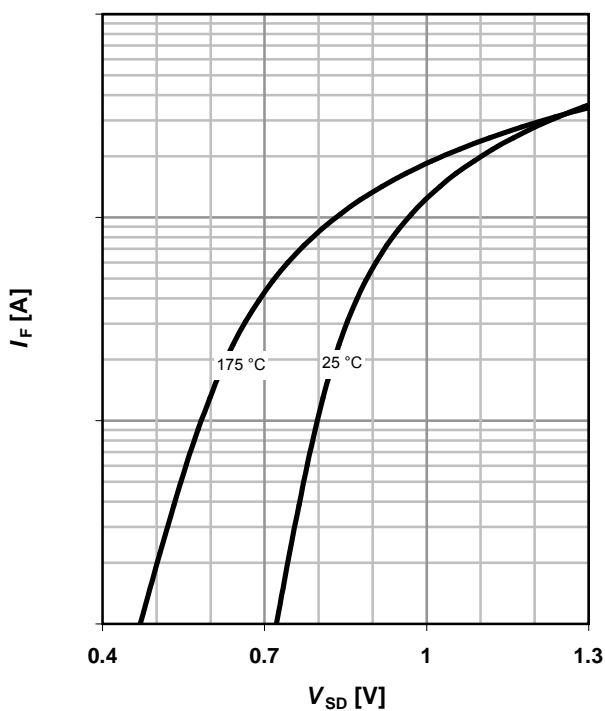
$C = f(V_{DS}); V_{GS} = 0 V; f = 1 MHz$



11 Typical forward diode characteristics

$I_F = f(V_{SD})$

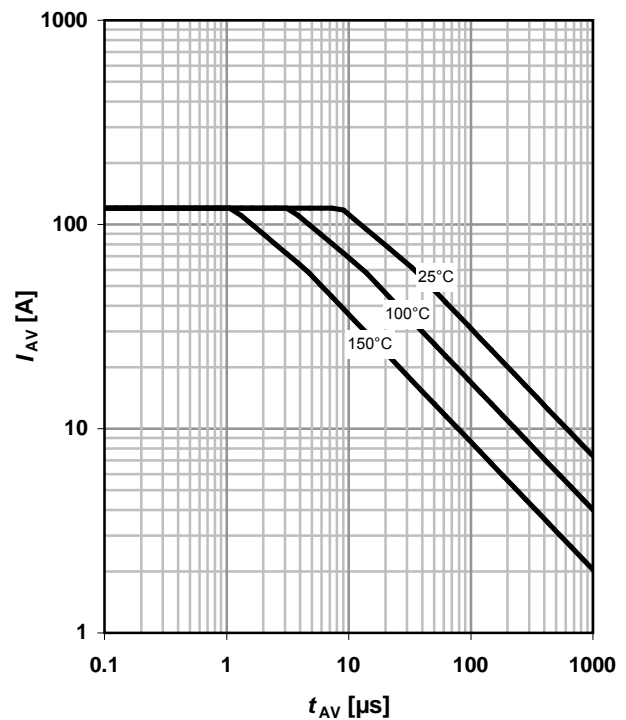
parameter: T_j



12 Typ. avalanche characteristics

$I_{AS} = f(t_{AV})$

parameter: $T_{j(start)}$



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Revision History

Version	Date	Changes
1.0	22.10.2013	Final Datasheet
1.1	07.04.2014	Added Avalanche Current